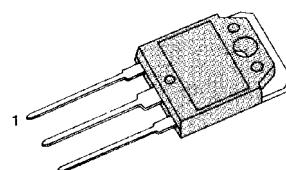
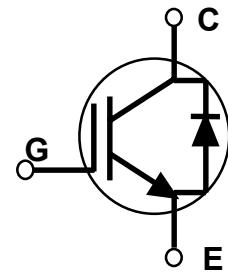


FEATURES

- * High Speed Switching
- * Low Saturation Voltage
: $V_{CE}(\text{sat}) = 2.0 \text{ V}$ (@ $I_C=40\text{A}$)
- * High Input Impedance
- *CO-PAK, IGBT with FRD
: $\text{Tr}_r = 50\text{nS}$ (typ.)

TO-3P**APPLICATIONS**

- * AC & DC Motor controls
- * General Purpose Inverters
- * Robotics , Servo Controls
- * Power Supply
- * Lamp Ballast

**ABSOLUTE MAXIMUM RATINGS**

Symbol	Characteristics	Rating	Units
V_{CES}	Collector-Emitter Voltage	600	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_c = 25^\circ\text{C}$	80	A
	Collector Current @ $T_c = 100^\circ\text{C}$	40	A
$I_{CM(1)}$	Pulsed Collector Current	220	A
I_F	Diode Continuous Forward Current @ $T_c = 100^\circ\text{C}$	25	A
I_{FM}	Diode Maximum Forward Current	280	A
P_D	Maximum Power Dissipation @ $T_c = 25^\circ\text{C}$	195	W
	Maximum Power Dissipation @ $T_c = 100^\circ\text{C}$	78	W
T_j	Operating Junction Temperature	-55 ~ 150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 ~ 150	$^\circ\text{C}$
T_L	Maximum Lead Temp. For Soldering Purposes, $\frac{1}{8}''$ from case for 5 seconds	300	$^\circ\text{C}$

Notes:(1) Repetitive rating : Pulse width limited by max. junction temperature

ELECTRICAL CHARACTERISTICS (IGBT PART)
(T_c=25°C, Unless Otherwise Specified)

Symbol	Characteristics	Test Conditions	Min	Typ	Max	Units
BV _{CES}	C - E Breakdown Voltage	V _{GE} = 0V , I _C = 250µA	600	-	-	V
ΔV _{CES/} ΔT _J	Temperature Coeff. of Breakdown Voltage	V _{GE} = 0V , I _C = 1mA	-	0.6	-	V/°C
V _{GE(th)}	G - E threshold voltage	I _C = 40mA , V _{CE} = V _{GE}	4.5	5.5	7.5	V
I _{CES}	Collector cutoff Current	V _{CE} = V _{CES} , V _{GE} = 0V	-	-	250	uA
I _{GES}	G - E leakage Current	V _{GE} = V _{GES} , V _{CE} = 0V	-	-	100	nA
V _{CE(sat)}	Collector to Emitter saturation voltage	Ic=40A, V _{GE} = 15V	-	2.0	2.6	V
		Ic=80A, V _{GE} = 15V	-	2.6	-	V
Cies	Input capacitance	V _{GE} = 0V , f = 1MHz V _{CE} = 30V	-	2790	-	pF
Coes	Output capacitance		-	347	-	pF
Cres	Reverse transfer capacitance		-	96	-	pF
td(on)	Turn on delay time	V _{CC} = 300V , I _C = 40A V _{GE} = 15V R _G = 5 Ω Inductive Load	-	17	-	ns
tr	Turn on rise time		-	33	-	ns
td(off)	Turn off delay time		-	97	130	ns
tf	Turn off fall time		-	70	140	ns
Eon	Turn on Switching Loss		-	0.12	-	mJ
Eoff	Turn off Switching Loss		-	0.68	-	mJ
Ets	Total Switching Loss		-	0.8	1.5	mJ
Qg	Total Gate Charge	Vcc = 300V V _{GE} = 15V	-	178	267	nC
Qge	Gate-Emitter Charge		-	40	60	nC
Qgc	Gate-Collector Charge		-	49	74	nC
Le	Internal Emitter Inductance	Measured 5mm from PKG	-	14	-	nH

ELECTRICAL CHARACTERISTICS (DIODE PART)
(T_c=25°C, Unless Otherwise Specified)

Symbol	Characteristics	Test Conditions		Min	Typ	Max	Units
VFM	Diode Forward Voltage	IF=25A	T _c =25 °C	-	1.4	1.7	V
			T _c =100 °C	-	1.3	-	
Tr _r	Diode Reverse Recovery Time	IF=25A, VR=200V -di/dt=200A/uS	T _c =25 °C	-	50	75	nS
			T _c =100 °C	-	105	-	
Irr	Diode Peak Reverse Recovery Current	IF=25A, VR=200V -di/dt=200A/uS	T _c =25 °C	-	4.5	10	A
			T _c =100 °C	-	8.5	-	
Qrr	Diode Reverse Recovery Charge	IF=25A, VR=200V -di/dt=200A/uS	T _c =25 °C	-	112	375	nC
			T _c =100 °C	-	420	-	

THERMAL RESISTANCE

Symbol	Characteristics	Min	Typ	Max	Units
R _θ JC	Junction-to-Case (IGBT)	-	-	0.64	°C/W
R _θ JC	Junction-to-Case (DIODE)	-	-	0.83	°C/W
R _θ JA	Junction-to-Ambient	-	-	40	°C/W
R _θ CS	Case-to-Sink	-	0.24	-	°C/W

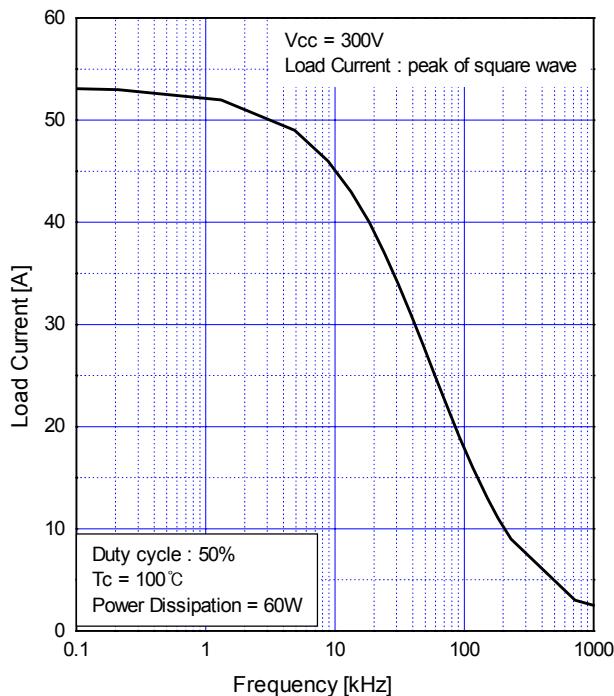


Fig.1 Typical Load Current vs. Frequency

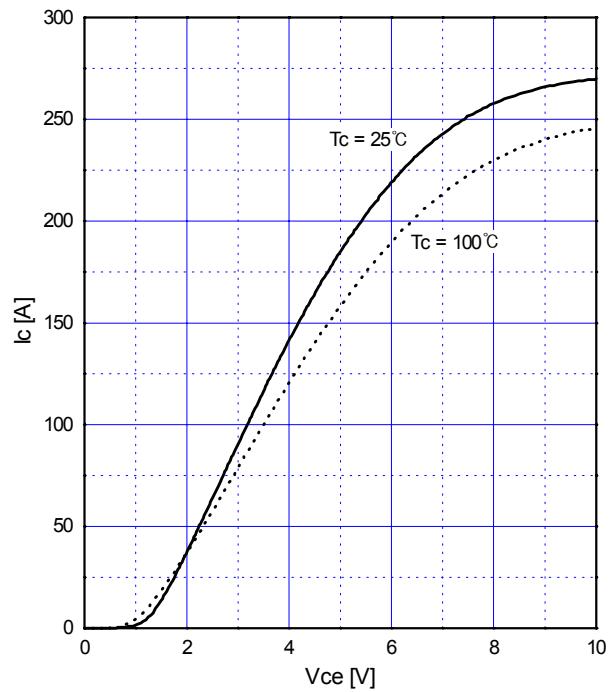


Fig.2 Typical Output Characteristics

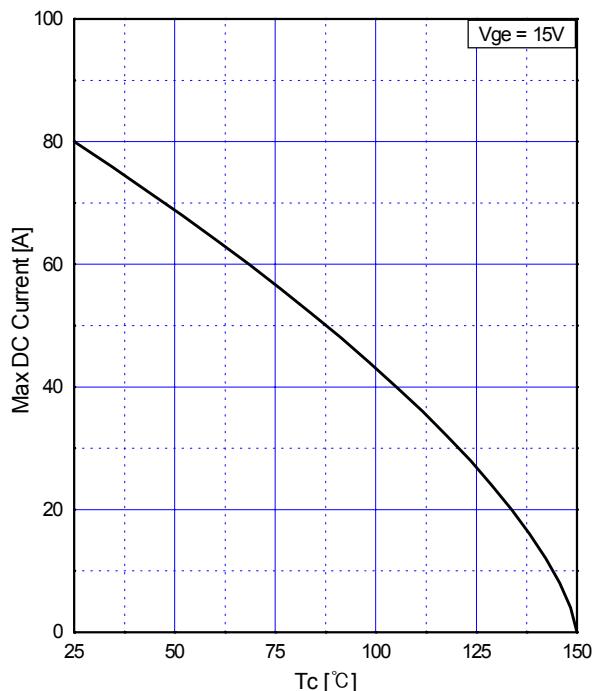


Fig.3 Maximum Collector Current vs. Case Temperature

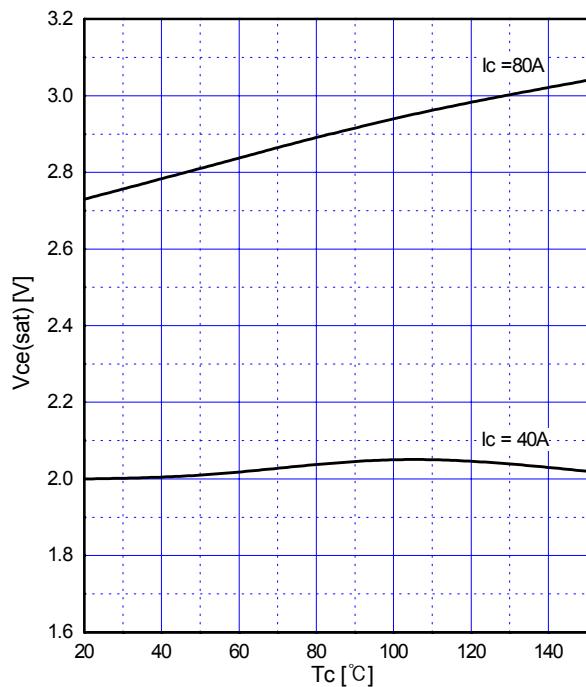


Fig.4 Collector to Emitter Voltage vs. Case Temperature

SGH80N60UF

N-CHANNEL IGBT

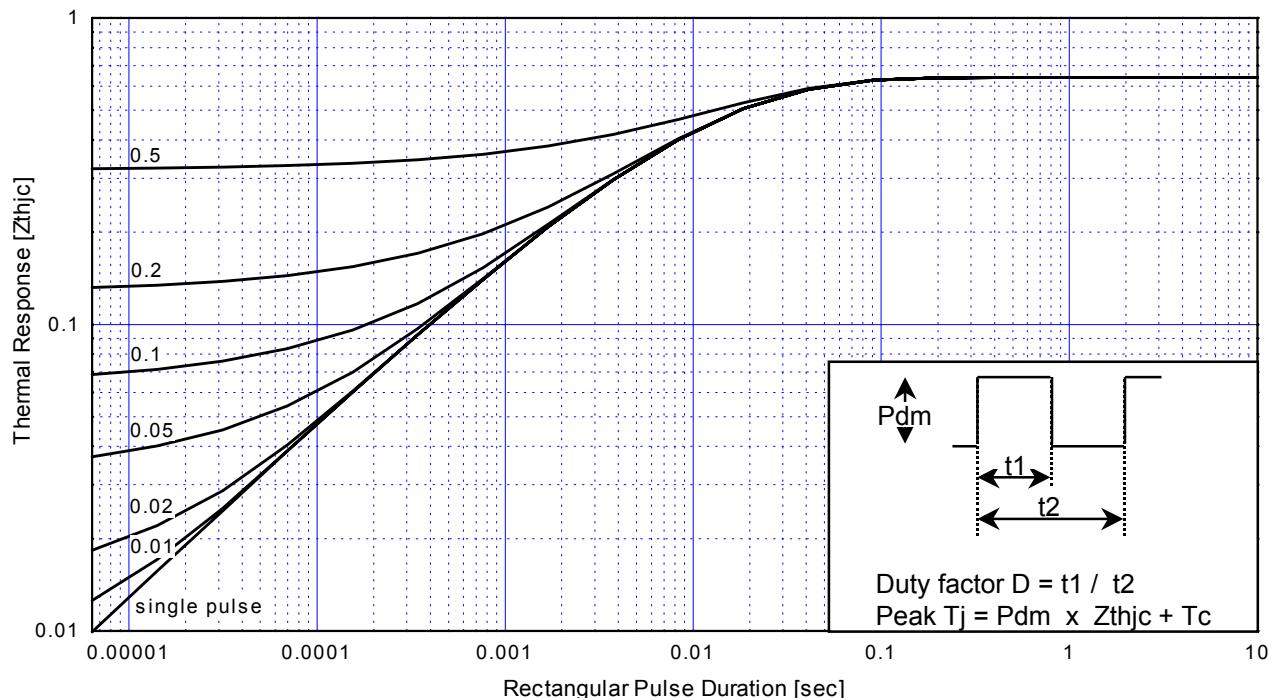


Fig.5 Maximum Effective Transient Thermal Impedance, Junction to Case

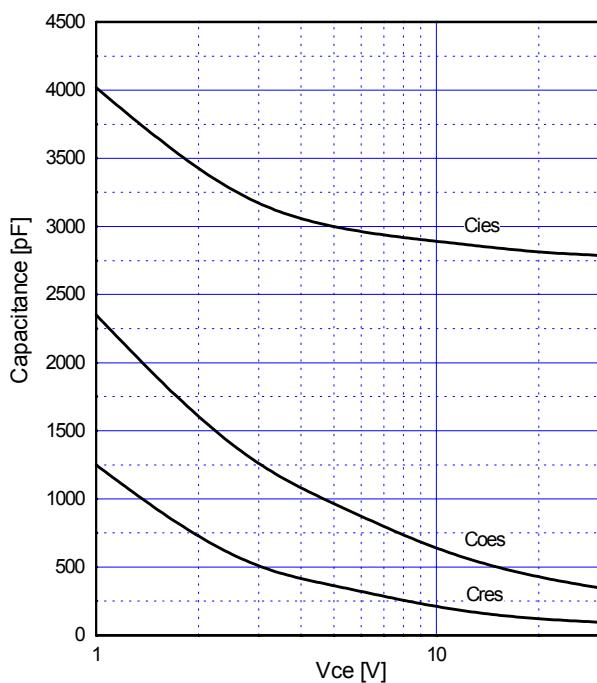


Fig.6 Typical Capacitance vs.
Collector to Emitter Voltage

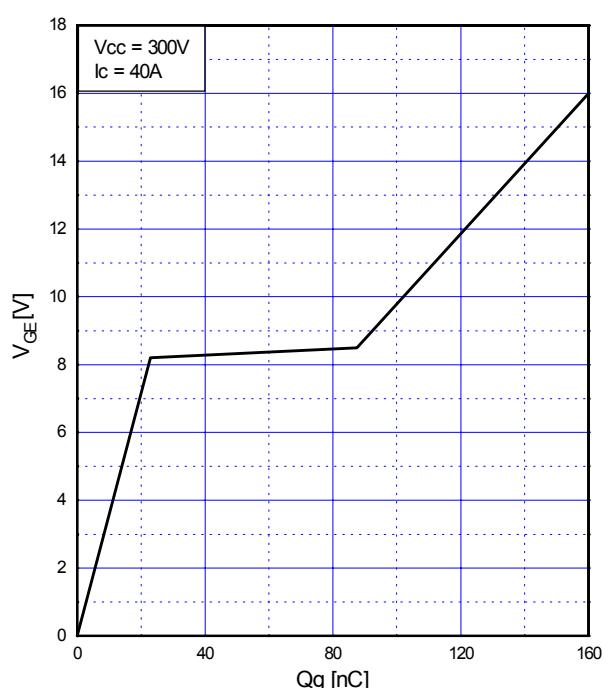


Fig.7 Typical Gate Charge vs.
Gate to Emitter Voltage

SGH80N60UF

N-CHANNEL IGBT

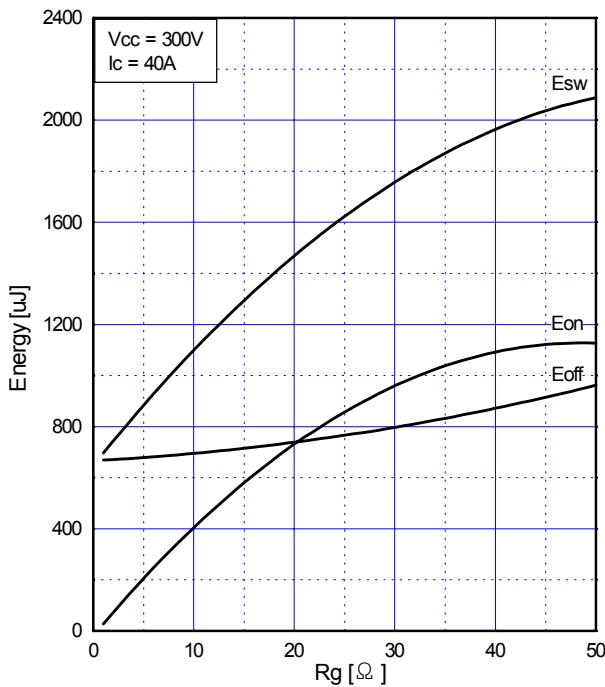


Fig.8 Typical Switching Loss vs.
Gate Resistance

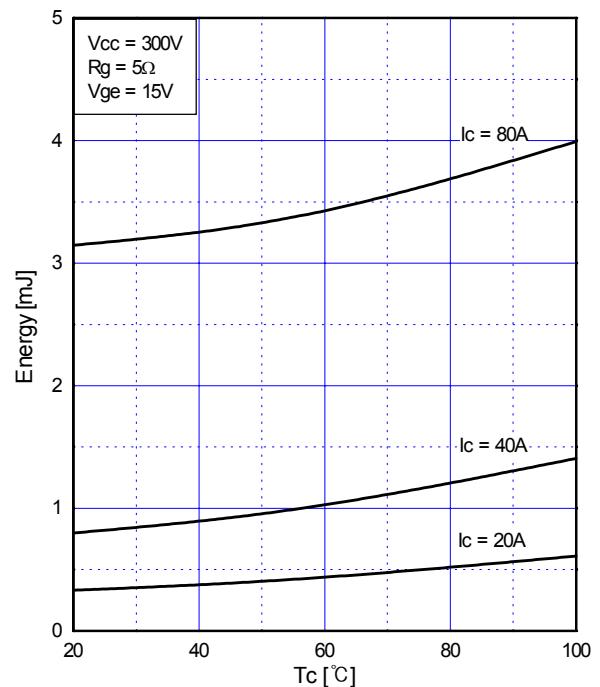


Fig.9 Typical Switching Loss vs.
Case Temperature

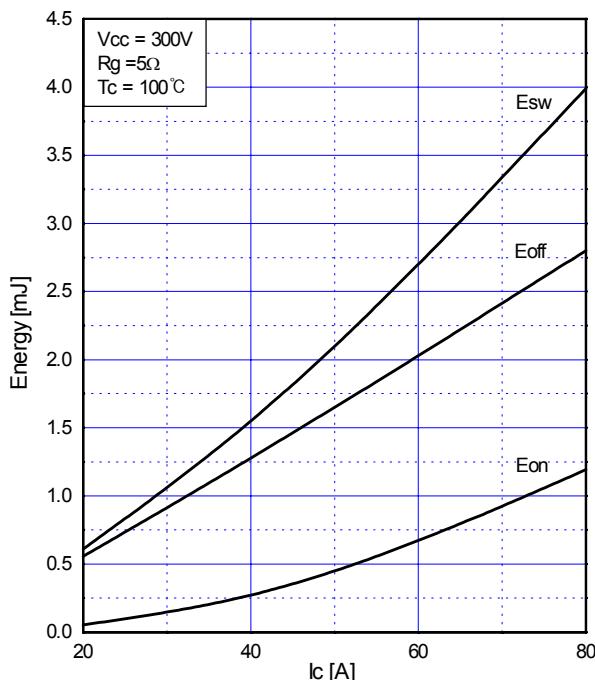


Fig.10 Typical Switching loss vs.
Collector to Emitter Current

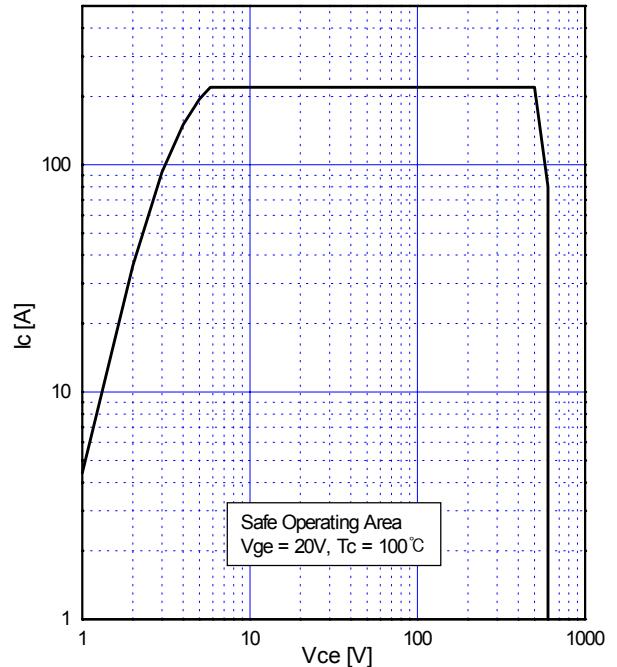


Fig.11 Turn-off SOA

SGH80N60UF

N-CHANNEL IGBT

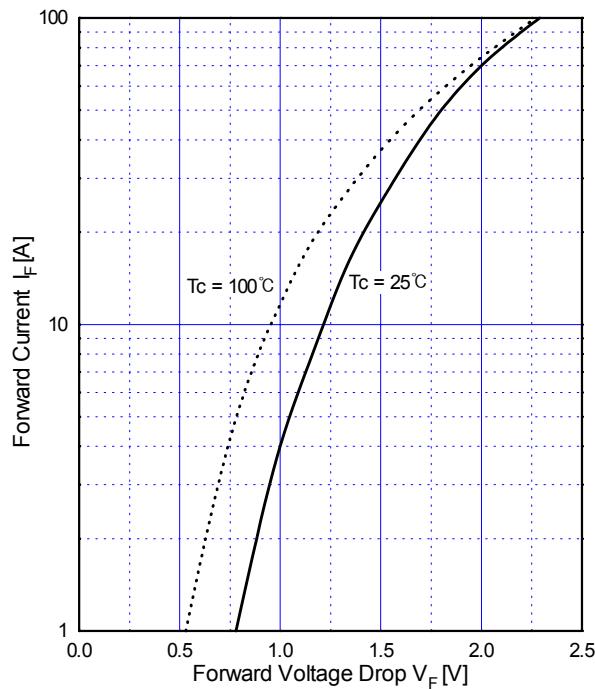


Fig.12 Typical Forward Voltage Drop
vs. Forward Current

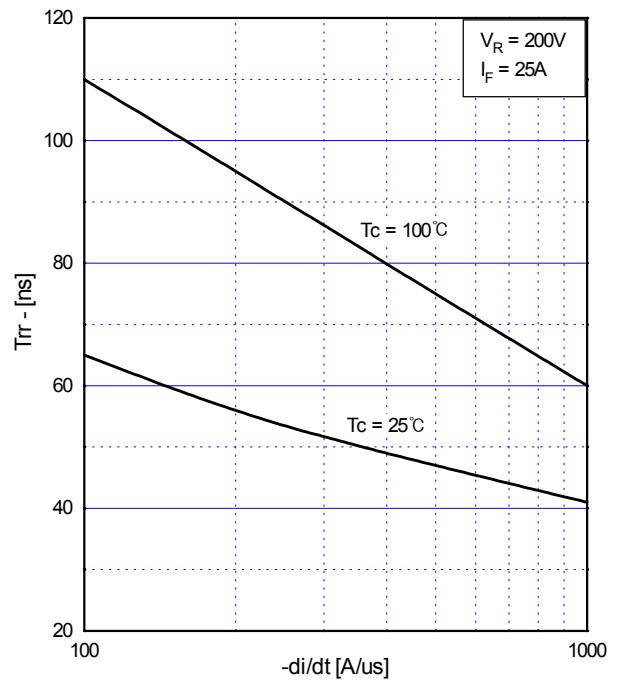


Fig.13 Typical Reverse Recovery Time
vs. $-di/dt$

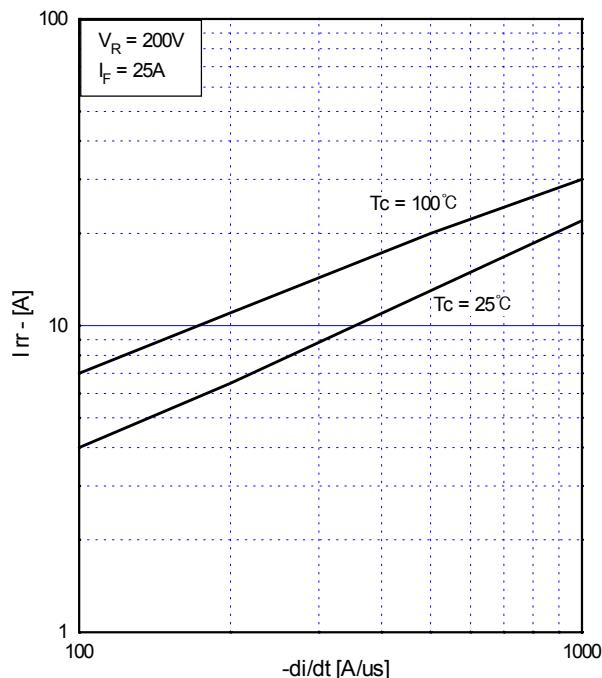


Fig.14 Typical Reverse Recovery Current
vs. $-di/dt$

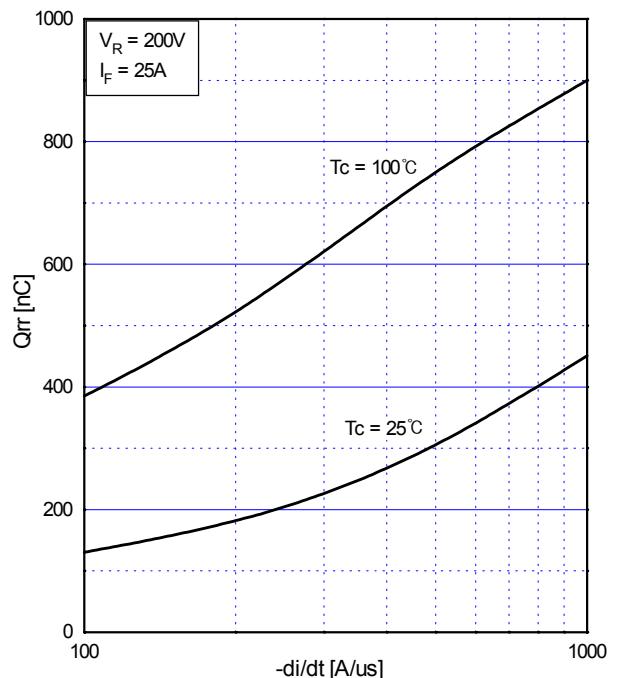


Fig.15 Typical Stored Charge vs. $-di/dt$